



END-LOOK PACKAGE PHOTO DIODE

● Features

1. Wide receiving angle.
2. Linear response vs. irradiance.
3. Fast switching time.
4. End-looking Package ideal for space Limited applications
5. Lens Appearance: Water Clear
6. This product doesn't contain restriction substance, comply ROHS standard

● Description

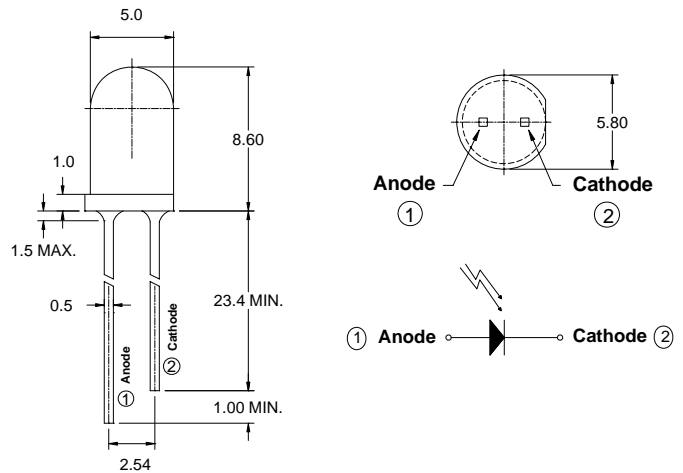
The HL-508GC05-QB device consists Of a PIN silicon photodiode molded in a black epoxy package which allows spectral response infrared light wavelengths.

The wide receiving angle provides relatively even reception over a large area. The end-looking package is designed for easy PC board mounting. This photodiode is mechanically and spectrally matched to BRIGHT's GaAs and GaAIAs series of infrared Emitting diodes.

● Absolute Maximum Ratings(Ta=25°C)

Parameter	Maximum Rating	Unit
Power Dissipation	100	mW
Reverse Breakdown Voltage	60V	
Operating Temperature	-40°C ~ +85°C	
Storage Temperature Range	-45°C ~ +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

● Package Dimensions:



NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25\text{mm}$ (0.01") unless otherwise specified.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.



● **Electrical Characteristics** (TA=25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Reverse light Current	I_L	-	80		μA	$V_R=5V$. $E_e=1mW/cm^2$
Reverse Dark Current	I_D	-	-	100	nA	$V_R=10V$. $E_e=0 mW/cm^2$
Reverse break down Voltage	$V_{(BR)}$	35	-	-	-	$I_R=100 \mu A$
Forward Voltage	V_F	-	-	1.3	V	$I_F=1mA$
Total Capacitance	C_T	-	9	-	PF	$V_R=5V$. $E_e=0$, $f=1.0MHZ$
Rise Time/Fall Time	tr/tf	-	50	-	ns	$V_R=20V$. $\lambda=940nm$. $RL=50 \Omega$

● **Typical Optical-Electrical Characteristic Curves**

